

3.6.3.1 Avionics LDMOS transistors (continued)

Type number	Product	f _{min} (MHz)	f _{max} (MHz)	P1dB (W)	Test signal performance				
					VDS (V)	η _D (%)	G _p (dB)	Test signal	Package version
BLF988(S)	Final	500	1000	600	50	58	19.8	Pulsed RF	SOT539
BLU6H0410L(S)-600P		400	900	600	50	58	20	Pulsed RF	SOT539
BLA6H0912L(S)-1000*		960	1215	1000	50	50	15.5	Pulsed RF	SOT539

3.6.3.2 L-band LDMOS transistors

Type number	Product	f _{min} (MHz)	f _{max} (MHz)	P1dB (W)	Test signal performance				
					VDS (V)	η _D (%)	G _p (dB)	Test signal	Package version
BLL6H0514-25	Driver	500	1400	25	50	50	19	Pulsed RF	SOT467
BLL8H0514-25		500	1400	25	50	59	21	Pulsed RF	SOT467
BLL6H0514L(S)-130	Final	500	1400	130	50	50	17	Pulsed RF	SOT1135
BLL8H0514L(S)-130		500	1400	130	50	50	17	Pulsed RF	SOT1135
BLL6G1214L(S)-250		1200	1400	250	36	45	15	Pulsed RF	SOT502
BLL6H1214L(S)-250		1200	1400	250	50	55	17	Pulsed RF	SOT502
BLL6H1214P2S-250		1200	1400	250	45	48	27	Pulsed RF	SOM039
BLL8H1214L(S)-250		1200	1400	250	50	55	17	Pulsed RF	SOT502
BLL6H1214(LS)-500		1200	1400	500	50	50	17	Pulsed RF	SOT539
BLL8H1214L(S)-500		1200	1400	500	50	50	17	Pulsed RF	SOT539

3.6.3.3 S-band LDMOS transistors

Type number	Product	f _{min} (MHz)	f _{max} (MHz)	P1dB (W)	Test signal performance				
					VDS (V)	η _D (%)	G _p (dB)	Test signal	Package version
BLS6G2731-6G	Driver	2700	3100	6	32	33	15	Pulsed RF	SOT975
BLS6G3135(S)-20		3100	3500	20	32	45	15.5	Pulsed RF	SOT608
BLS6G2735L(S)-30		2700	3500	30	32	50	13	Pulsed RF	SOT1135
BLS7G2325L-105	Final	2300	2500	105	30	55	16.5	Pulsed RF	SOT502
BLS6G2731(S)-120		2700	3100	120	32	48	13.5	Pulsed RF	SOT502
BLS6G3135(S)-120		3100	3500	120	32	43	11	Pulsed RF	SOT502
BLS6G2731S-130		2700	3100	130	32	50	12	Pulsed RF	SOT922
BLS6G2933S-130		2900	3300	130	32	47	12.5	Pulsed RF	SOT922
BLS7G2933S-150		2900	3300	150	32	47	13.5	Pulsed RF	SOT922
BLS7G2730L(S)-200P		2700	3000	200	32	48	12	Pulsed RF	SOT539
BLS7G3135LS-200		3100	3500	200	32	43	12	Pulsed RF	SOT502
BLS7G2729L(S)-350P		2700	2900	350	32	50	13	Pulsed RF	SOT539
BLS7G3135L(S)-350P		3100	3500	350	32	43	12	Pulsed RF	SOT539
BLS8G2731L(S)-400P*		2700	3100	400	32	40	11	Pulsed RF	SOT539

3.6.4 Gallium Nitride (GaN) RF power amplifiers

Device naming conventions for GaN RF power amplifiers

C	L	F	1G	0040	S	50	P
P: push-pull indicator, P = push-pull type; no P means single-ended transistor							
2 to 1500: nominal P3dB in Watts; eg 50 = 50 W							
S: earless type, S = earless; no S means eared package							
35 to 60: upper frequency, 10x GHz value: 35 = 3.5 GHz; 60 = 6.0 GHz							
00 to 40: lower frequency, 10x GHz value: 00 = 0 GHz or DC; 40 = 4.0 GHz							
1G: technology generation: 1G = 1st generation							
F: package style: F = ceramic, P = overmolded plastic							
L: high-frequency power transistor							
C: primary material identifier: C = wide band-gap compound materials, eg GaN							

Type number	Product	f _{min} (MHz)	f _{max} (MHz)	P1dB (W)	Test signal performance				
					VDS (V)	η _D (%)	G _p (dB)	Test signal	Package version
CLF1G0060(S)-10*	Driver	0	6000	10	50	33.2	17	Pulsed RF	SOT1227
CLF1G0060(S)-30*		0	6000	30	50	59	15.9	Pulsed RF	SOT1227
CLF1G0035-50	Driver/final	0	3500	50	50	49	13	Pulsed RF	SOT467
CLF1G0035S-50*		0	3500	50	50	49	13	Pulsed RF	SOT467
CLF1G0035-100	Final	0	3500	100	50	59.5	13.9	Pulsed RF	SOT467
CLF1G0035S-100*		0	3500	100	50	59.5	13.9	Pulsed RF	SOT467
CLF1G0035-100P*		0	3500	100	50	50.1	12.7	Pulsed RF	SOT1228
CLF1G0035S-100P*		0	3500	100	50	50.1	12.7	Pulsed RF	SOT1228

* Check status in section 3.1, as this type is not yet released for mass production